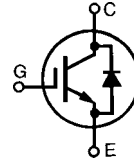


# HiPerFAST™ IGBT with Diode

## Combi Pack

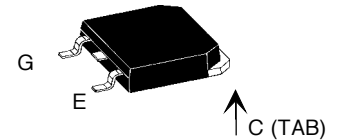
IXGH 30N60BU1  
IXGT 30N60BU1

$V_{CES} = 600 \text{ V}$   
 $I_{C25} = 60 \text{ A}$   
 $V_{CE(sat)} = 1.8 \text{ V}$   
 $t_{fi} = 100 \text{ ns}$

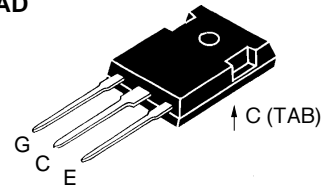


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	60	A
$I_{C110}$	$T_C = 110^\circ\text{C}$	30	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	120	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 33 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 60$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	200	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-268	4	g
	TO-247 AD	6	g

TO-268  
(IXGT)



TO-247 AD



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

### Features

- International standard packages JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High frequency IGBT and antiparallel FRED in one package
- High current handling capability
- Newest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

### Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

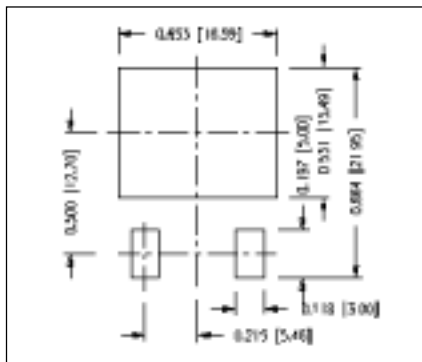
### Advantages

- Space savings (two devices in one package)
- High power density
- Optimized  $V_{CE(sat)}$  and switching speeds for medium frequency applications

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 750 \mu\text{A}, V_{GE} = 0 \text{ V}$ $BV_{CES}$ temperature coefficient	600	0.072	V %/K
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$ $V_{GE(th)}$ temperature coefficient	2.5	-0.286	V %/K
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$			500 $\mu\text{A}$ 3 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15 \text{ V}$			1.8 V
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15 \text{ V}$ $T_J = 150^\circ\text{C}$			2.0 V

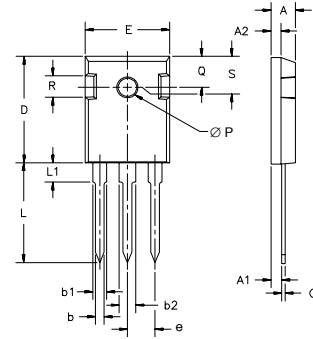
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C110}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$		25	S
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		2710	pF
$C_{oes}$			240	pF
$C_{res}$			50	pF
$Q_g$	$I_C = I_{C110}$ ; $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		110	150 nC
$Q_{ge}$			22	35 nC
$Q_{gc}$			40	75 nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C110}$ ; $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ ; $R_G = R_{off} = 4.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		25	ns
$t_{ri}$			30	ns
$t_{d(off)}$			130	220 ns
$t_{fi}$			100	190 ns
$E_{off}$			1.0	2.0 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = I_{C110}$ ; $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ ; $R_G = R_{off} = 4.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		25	ns
$t_{ri}$			35	ns
$E_{on}$			1	mJ
$t_{d(off)}$			200	ns
$t_{fi}$			230	ns
$E_{off}$		2.5	mJ	
$R_{thJC}$				0.62 K/W
$R_{thCK}$			0.25	K/W

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = I_{C110}$ ; $V_{GE} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.6 V
$I_{RM}$	$I_F = I_{C110}$ ; $V_{GE} = 0\text{ V}$ , $-di_F/dt = 240\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$		10	15 A
$t_{rr}$	$I_F = 1\text{ A}$ ; $-di/dt = 100\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$		35	50 ns
$R_{thJC}$				1 K/W



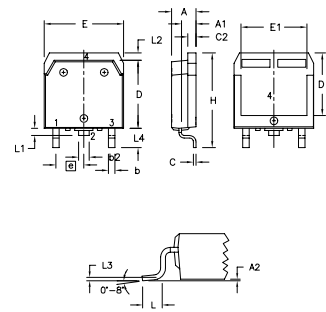
Min Recommended Footprint

### TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

### TO-247 AA (D<sup>3</sup> PAK)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A <sub>1</sub>	2.7	2.9	.106	.114
A <sub>2</sub>	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b <sub>2</sub>	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E <sub>1</sub>	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25 BSC		.010 BSC
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 1. Saturation Voltage Characteristics

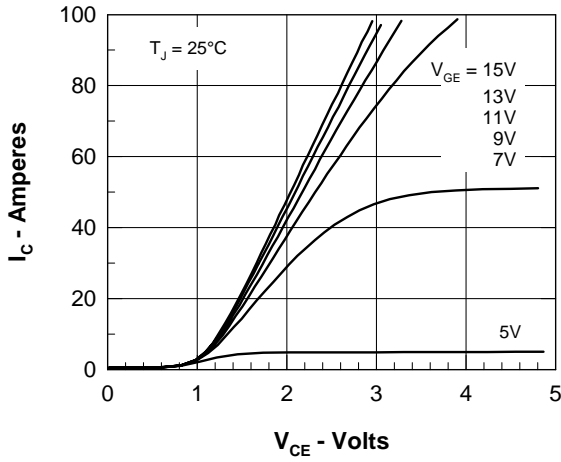


Fig. 2. Extended Output Characteristics

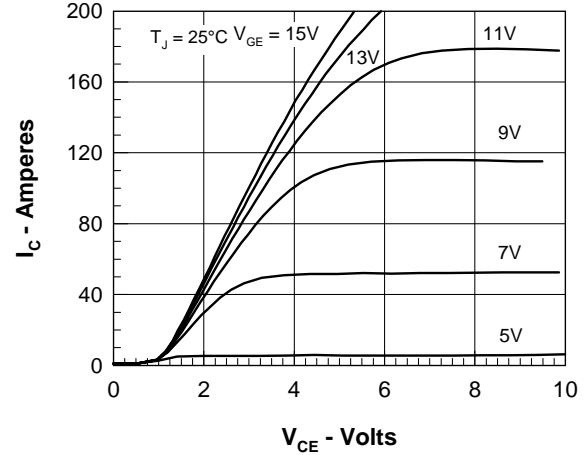


Fig. 3. Saturation Voltage Characteristics

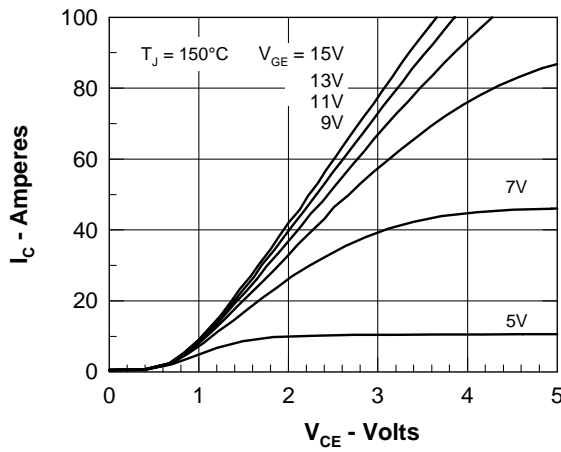


Fig. 4. Temperature Dependence of  $V_{CE(sat)}$

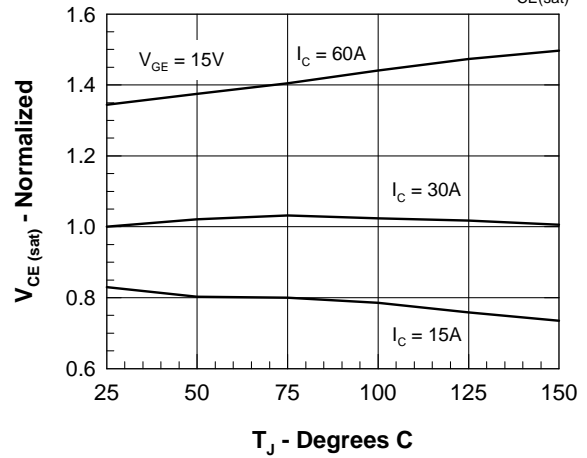


Fig. 5. Admittance Curves

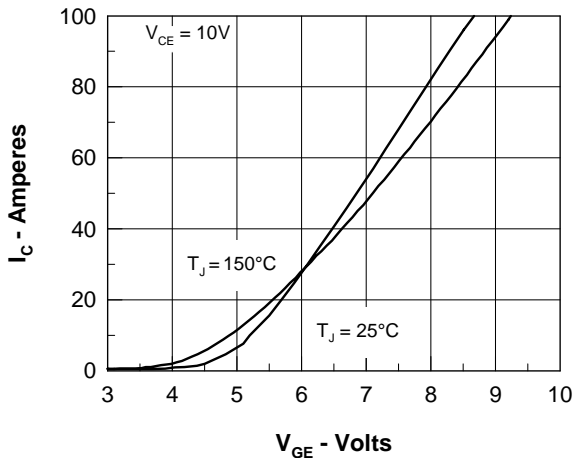


Fig. 6. Temperature Dependence of  $BV_{DSS}$  &  $V_{GE(th)}$

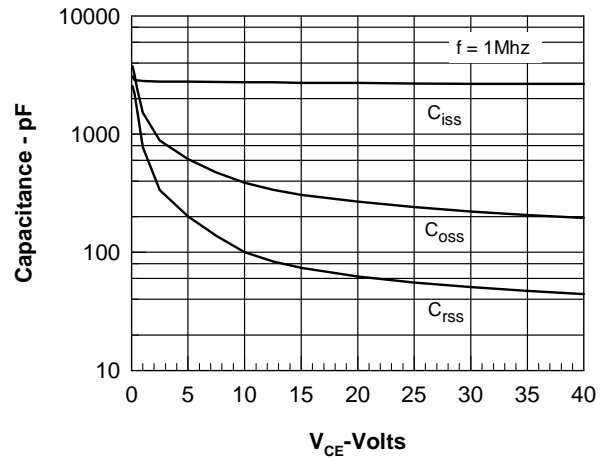


Fig. 7. Dependence of  $E_{(OFF)}$  and  $E_{(ON)}$  on  $I_C$ .

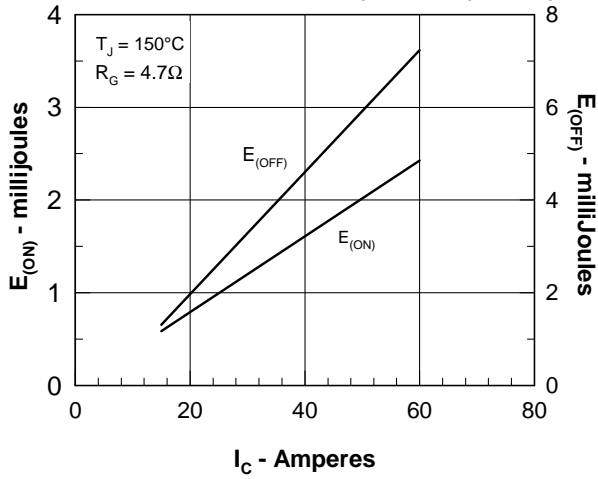


Fig. 8. Dependence of  $E_{(OFF)}$  on  $R_G$ .

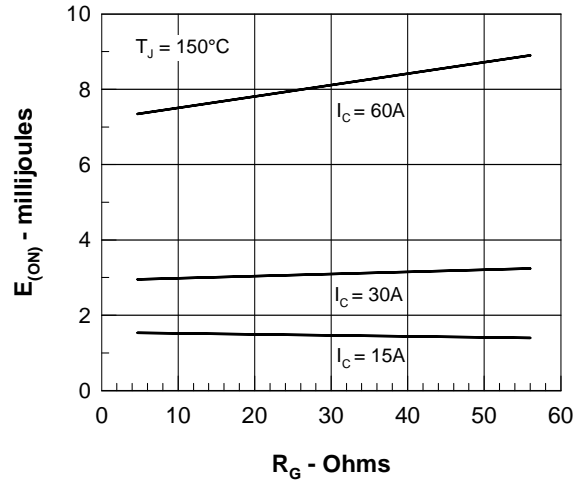


Fig. 9. Gate Charge

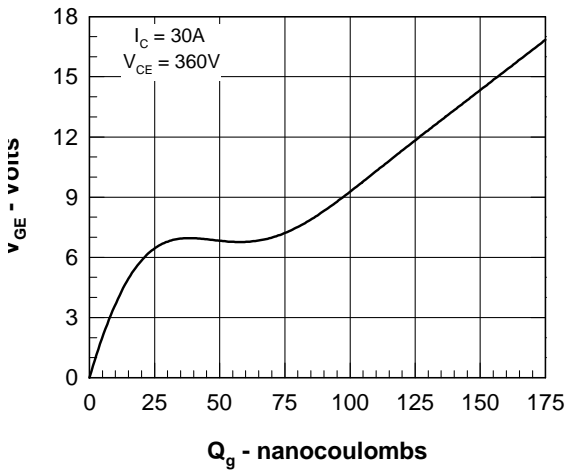


Fig. 10. Turn-off Safe Operating Area

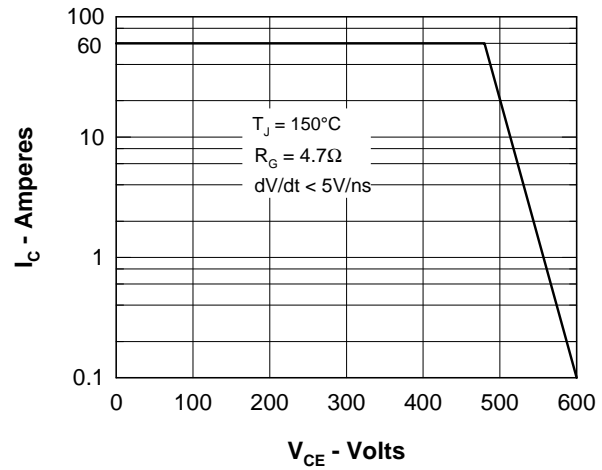
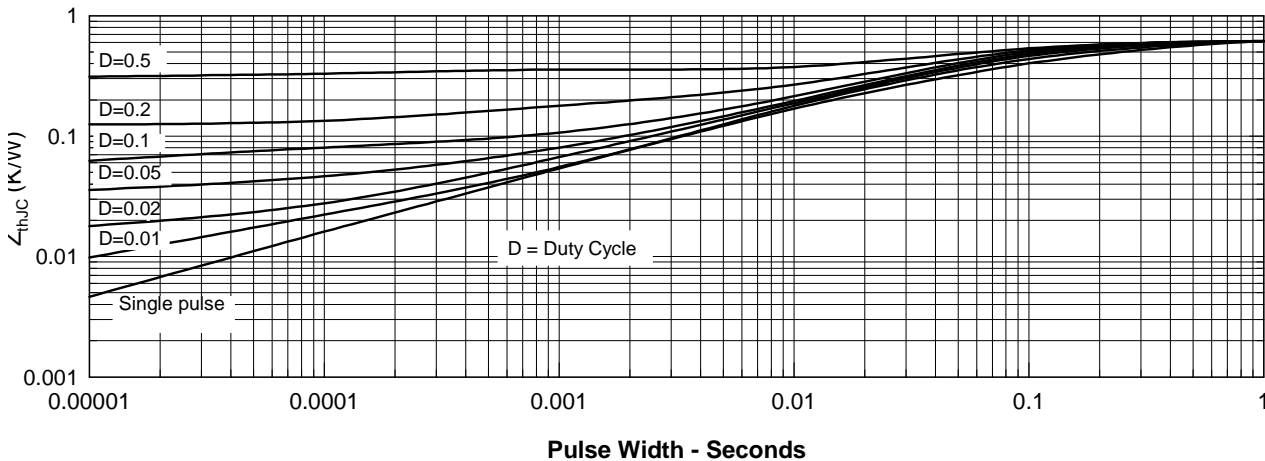


Fig. 11. IGBT Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

Fig. 12. Forward current versus voltage drop.

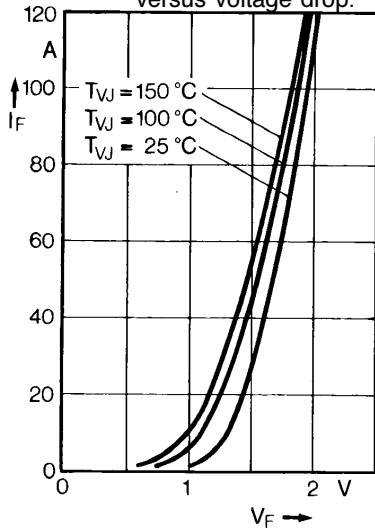


Fig. 13. Recovery charge versus  $-di_F/dt$ .

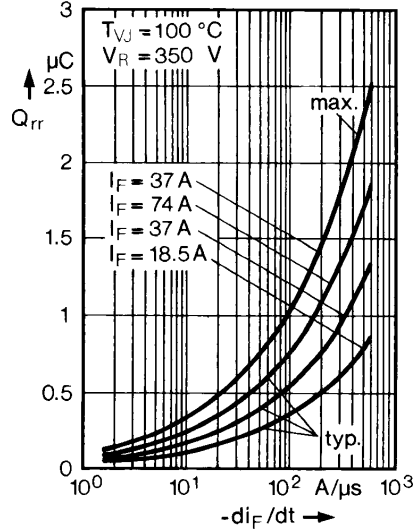


Fig. 14. Peak reverse current versus  $-di_F/dt$ .

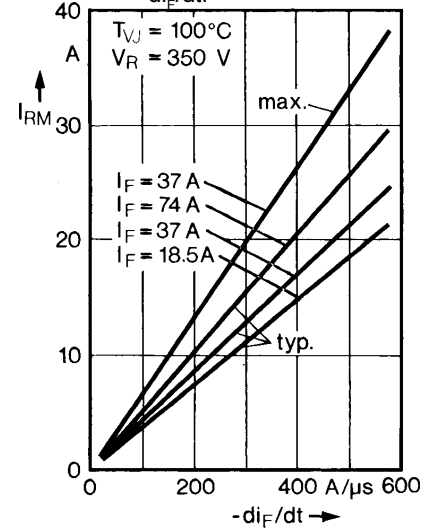


Fig. 15. Dynamic parameters versus junction temperature.

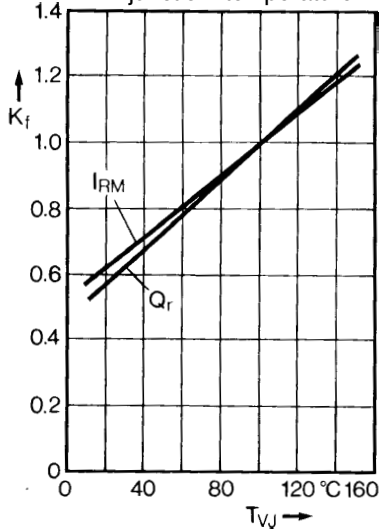


Fig. 16. Reverse recovery time vs  $-di_F/dt$ .

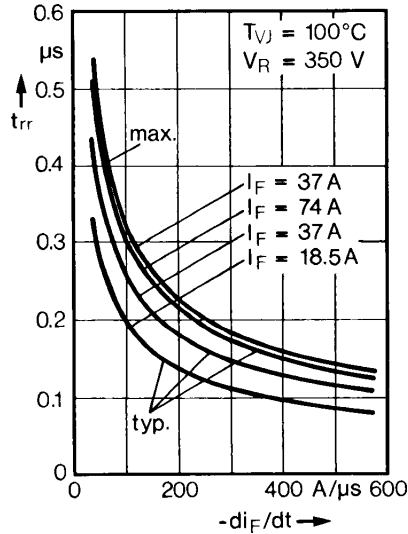


Fig. 17. Forward voltage recovery and time versus  $-di_F/dt$ .

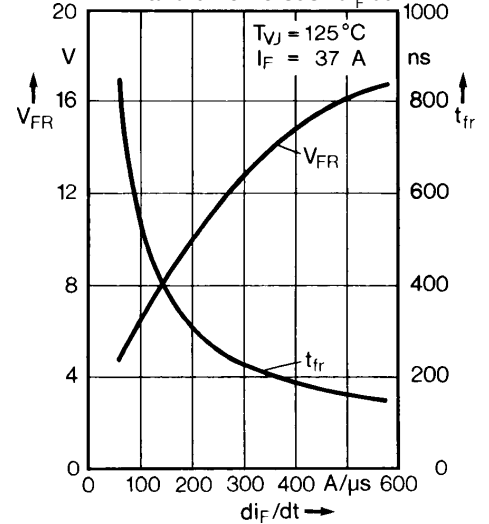


Fig. 18. Transient thermal resistance junction to case.

